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December 2015



# FAN48619 Fixed-Output Synchronous TinyBoost® Regulator

#### **Features**

Input Voltage Range: 2.7 V to 4.5 V

Output Voltage: 5.0 V

1000 mA Max. Load Capability

PWM Only

Up to 97% Efficient

Forced Pass-Through Operation via EN Pin

Internal Synchronous Rectification

True Load Disconnect

Short-Circuit Protection

 Three External Components: 2016 (Metric) 0.47 µH Inductor, 0402 Case Size Input / Output Capacitors

## **Applications**

- Class-D Audio Amplifier
- Boost for Low-Voltage Li-Ion Batteries
- Smart Phones, Tablets, Portable Devices
- RF Applications
- NFC Applications

## Description

The FAN48619 is a low-power PWM only boost regulator designed to provide a minimum voltage-regulated rail from a standard single-cell Li-lon battery and advanced battery chemistries. Even below the minimum system battery voltage, the device maintains the output voltage regulation for an output load current of 1000 mA. The combination of built-in power transistors, synchronous rectification, and low supply current suit the FAN48619 for battery-powered applications.

The FAN48619 is available in a 9-bump, 0.4 mm pitch, (1.215 x 1.215 mm) Wafer-Level Chip-Scale Package (WLCSP).

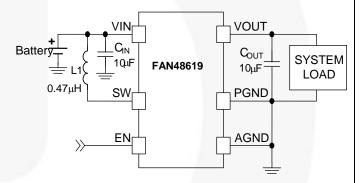


Figure 1. Typical Application

## **Ordering Information**

Part Number	V <sub>out</sub>	Operating Temperature	Package Packir		Device Marking
FAN48619UC50X	5.0 V	-40°C to 85°C	9-Bump, 0.4 mm Pitch, WLCSP Package	Tape and Reel	KP

#### Note:

1. The FAN48619UC50X includes backside lamination.

## **Block Diagrams**

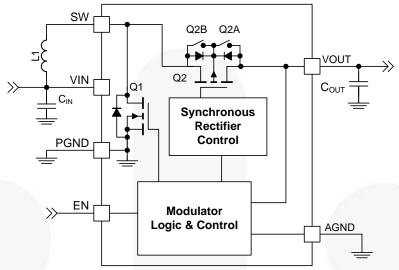


Figure 2. IC Block Diagram

Table 1. Recommended Components

Component	Description	Vendor	Parameter	Тур.	Unit
1.4	200/ F 2A 2016 1 0mm Height	DFE201610E-R47M	Inductance	470	nH
L1	20%, 5.3A, 2016, 1.0mm Height	TOKO	DCR (Series R)	26	mΩ
C <sub>IN</sub>	20%, 6.3 V, X5R, 0402 (1005)	C1005X5R0J106M050BC TDK	Capacitance	10	μF
C <sub>OUT</sub>	20%, 6.3 V, X5R, 0402 (1005)	C1005X5R0J106M050BC	Capacitance	10	μΓ

## **Pin Configuration**

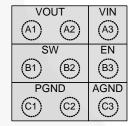


Figure 3. Top View

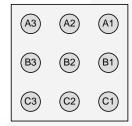


Figure 4. Bottom View

## **Pin Definitions**

Pin #	Name	Description				
A1, A2	VOUT	put Voltage. This pin is the output voltage terminal; connect directly to C <sub>OUT</sub> .				
А3	VIN	it Voltage. Connect to Li-lon battery input power source and C <sub>IN</sub> .				
B1, B2	SW	ritching Node. Connect to inductor.				
В3	EN	<b>Enable</b> . When this pin is HIGH, the circuit is enabled. After part is engaged, pin forces part into Forced-Pass-Through Mode when EN pin is pulled LOW.				
C1, C2 PGND Power Ground. This is the power return for the IC. C <sub>OUT</sub> capacitor should be returned with the short path possible to these pins.		<b>Power Ground</b> . This is the power return for the IC. C <sub>OUT</sub> capacitor should be returned with the shortest path possible to these pins.				
С3	AGND	<b>Analog Ground</b> . This is the signal ground reference for the IC. All voltage levels are measured with respect to this pin – connect to PGND at a single point.				

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Para	Min.	Max.	Unit	
V <sub>IN</sub>	Voltage on VIN Pin			6.0	V
V <sub>OUT</sub>	Voltage on VOUT Pin	Voltage on VOUT Pin			V
Vou	SW Node	DC	-0.3	6.0	V
V <sub>SW</sub>	Svv Node	Transient: 10 ns, 3 MHz	-1.0	8.0	V
V <sub>CC</sub>	Voltage on Other Pins		-0.3	6.0 <sup>(2)</sup>	<b>V</b>
ESD	Electrostatic Discharge Protection Level  Human Body Model, ANSI/ESDA/JEDEC JS-001-2012		2.0		kV
		Charged Device Model per JESD22-C101	1	.0	
TJ	Junction Temperature		-40	+150	°C
T <sub>STG</sub>	Storage Temperature		-65	+150	°C
$T_L$	Lead Soldering Temperature, 10 Seconds			+260	°C

#### Note:

2. Lesser of 6.0 V or  $V_{IN}$  + 0.3 V.

## **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Unit
V <sub>IN</sub>	Supply Voltage	2.7	4.5	V
I <sub>OUT</sub>	Maximum Output Current	1000		mA
T <sub>A</sub>	Ambient Temperature	-40	+85	°C
TJ	Junction Temperature	-40	+125	°C

## **Thermal Properties**

Junction-to-ambient thermal resistance is a function of application and board layout. This data is measured with four-layer 2s2p boards with vias in accordance to JEDEC standard JESD51. Special attention must be paid not to exceed junction temperature,  $T_{J(max)}$ , at a given ambient temperature,  $T_A$ .

Symbol	Parameter	Typical	Unit
ӨЈА	Junction-to-Ambient Thermal Resistance	101	°C/W

## **Electrical Specifications**

Recommended operating conditions, unless otherwise noted, circuit per Figure 1,  $V_{OUT} = 5.0 \text{ V}$ . Typical, minimum and maximum values are given at  $V_{IN} = 3.6 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ ,  $-40^{\circ}\text{C}$ , and  $+85^{\circ}\text{C}$ .

Symbol	Parameter	Conditions		Тур.	Max.	Units
Power Sup	oply				I	
	V Quiacant Current	I <sub>OUT</sub> = 0 mA, EN = 1.8 V, No Switching		95		^
ΙQ	V <sub>IN</sub> Quiescent Current	Forced Pass-Through EN=0 V, $V_{OUT} = V_{IN}$		3.5		<u>μ</u> Α
V <sub>UVLO</sub>	Under-Voltage Lockout	V <sub>IN</sub> Rising		2.20		V
V <sub>UVLO_HYS</sub>	Under-Voltage Lockout Hysteresis			150		mV
Inputs						
V <sub>IH</sub>	Enable HIGH Voltage		1.05			V
V <sub>IL</sub>	Enable LOW Voltage				0.4	V
Outputs						
$V_{REG}$	Output Voltage Accuracy DC(3)	2.7 V ≤ V <sub>IN</sub> ≤ 4.5 V	-2		+2	%
Timing						
f <sub>SW</sub>	Switching Frequency	I <sub>OUT</sub> = 300 mA	1.8	2.3	2.8	MHz
tss <sup>(4)</sup>	EN HIGH to 95% of Regulation	I <sub>OUT</sub> = 150 mA		425		μS
t <sub>RST</sub> <sup>(4)</sup>	FAULT Restart Timer			20		ms
Power S	tage		1			
$R_{DS(ON)N}$	N-Channel Boost Switch R <sub>DS(ON)</sub>			63		mΩ
R <sub>DS(ON)P</sub>	P-Channel Sync. Rectifier R <sub>DS(ON)</sub>			52		mΩ
Mataa.						

#### Notes

- 3. DC I<sub>LOAD</sub> from 0 to 1000 mA. V<sub>OUT</sub> measured from mid-point of output voltage ripple. Effective capacitance of  $C_{OUT} \ge 2 \mu F$ .
- 4. Guaranteed by design and characterization; not tested in production.

## **Typical Performance Characteristics**

Unless otherwise specified;  $V_{IN}$  = 3.6 V,  $V_{OUT}$  = 5.0 V,  $T_A$  = 25°C, and circuit according to Figure 1. Components:  $C_{IN}$  =  $C_{OUT}$  = 10  $\mu$ F (0402, X5R, 6.3 V, C1005X5R0J106M050BC), L1 = 470 nH (2016, 26 m $\Omega$ , DFE201610E-R47M).

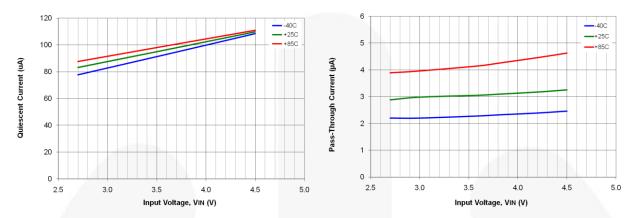
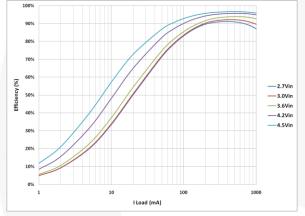


Figure 5. Quiescent Current (No Switching) vs. Input Voltage and Temperature

Figure 6. Pass-Through Current vs. Input Voltage and Temperature

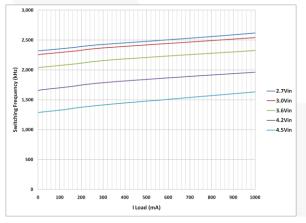


90%
80%
70%
60%
40%
-85C
-25C
--40C

10%
10%
1 10 100 1000

Figure 7. Efficiency vs. Load Current and Input Voltage

Figure 8. Efficiency vs. Load Current and Temperature



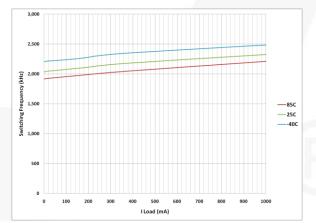
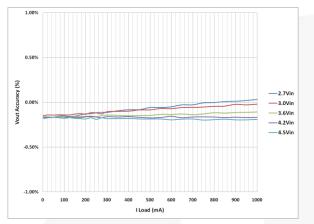


Figure 9. Switching Frequency vs. Load Current and Input Voltage

Figure 10. Switching Frequency vs. Load Current and Temperature

## **Typical Performance Characteristics**

Unless otherwise specified;  $V_{IN}$  = 3.6 V,  $V_{OUT}$  = 5.0 V,  $T_A$  = 25°C, and circuit and components according to Figure 1. Components:  $C_{IN}$  =  $C_{OUT}$  = 10  $\mu$ F (0402, X5R, 6.3 V, C1005X5R0J106M050BC), L1 = 470nH (2016, 26 m $\Omega$ , DFE201610E-R47M).



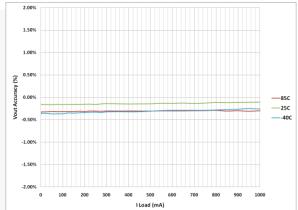
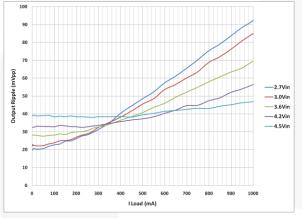


Figure 11. Output Regulation vs. Load Current and Input Voltage

Figure 12. Output Regulation vs. Load Current and Temperature



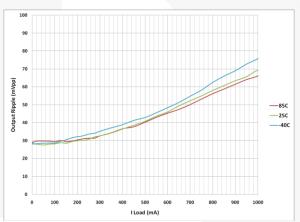
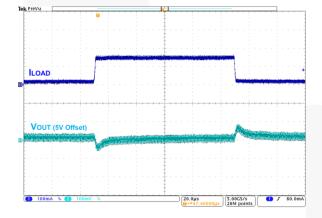


Figure 13. Output Ripple vs. Load Current and Input Voltage

Figure 14. Output Ripple vs. Load Current and Temperature



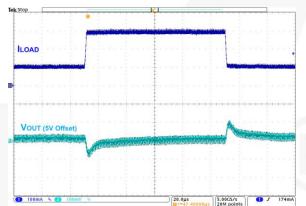


Figure 15. Load Transient, 20 <-->150 mA, 1 µs Edge

Figure 16. Load Transient, 100 <--> 300 mA, 1 μs Edge

## **Typical Performance Characteristics**

Unless otherwise specified;  $V_{IN}$  = 3.6 V,  $V_{OUT}$  = 5.0 V,  $T_A$  = 25°C, and circuit and components according to Figure 1. Components:  $C_{IN}$  =  $C_{OUT}$  = 10  $\mu$ F (0402, X5R, 6.3 V, C1005X5R0J106M050BC), L1 = 470nH (2016, 26 m $\Omega$ , DFE201610E-R47M).

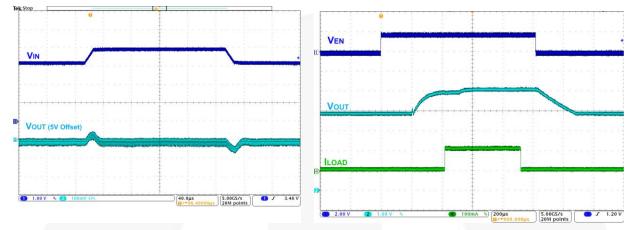


Figure 17. Line Transient, 3.2 V <-->3.9 V, 10 µs Edge, Figure 18. Pass-Through Mode <--> Boost Mode with 150 mA Load Load Transient , 10 <-->150 mA, 1 µs Edge

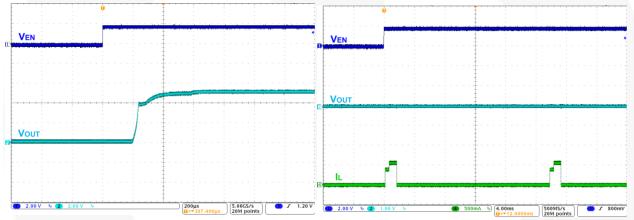


Figure 19. Startup, 150 mA Load

Figure 20. Fault Restart

## **Circuit Description**

FAN48619 is a synchronous PWM Only boost regulator. The regulator's Pass-Through Mode automatically activates when  $V_{\text{IN}}$  is above the boost regulator's set point.

**Table 2. Operating Modes** 

Mode Description		Invoked When:
LIN	Linear Startup	V <sub>IN</sub> > V <sub>OUT</sub>
SS	Boost Soft-Start	V <sub>IN</sub> < V <sub>OUT</sub> < V <sub>OUT</sub> (TARGET)
BST	Boost Operating Mode	V <sub>OUT</sub> = V <sub>OUT(TARGET)</sub>
PT	Pass-Through Mode	V <sub>IN</sub> > V <sub>OUT(TARGET)</sub> or when EN is pulled LOW after initial startup

#### **Boost Mode Regulation**

The FAN48619 uses a current-mode modulator to achieve excellent transient response.

Table 3. Boost Startup Sequence

Start Mode	Entry	Exit	End Mode	Timeout (µs)
	V <sub>IN</sub> >	$V_{OUT} > V_{IN}$ -300 mV	SS	
LIN1	V <sub>UVLO</sub> , EN=1	Timeout	LIN2	512
LIN2	LIN1 Exit	$V_{OUT} > V_{IN}$ -300 mV	SS	
LINZ		Timeout	FAULT	1024
SS	LIN1 or	V <sub>OUT</sub> =V <sub>OUT</sub> (TARGET)	BST	
33	LIN2 Exit	Overload Timeout	FAULT	64

#### **LIN Mode**

When EN is HIGH and  $V_{\text{IN}} > V_{\text{UVLO}}$ , the regulator first attempts to bring  $V_{\text{OUT}}$  within 300 mV of  $V_{\text{IN}}$  by using the internal fixed-current source from VIN (Q2). The current is limited to the LIN1 set point.

If  $V_{\text{OUT}}$  reaches  $V_{\text{IN}}\text{-}300$  mV during LIN1 Mode, the SS Mode is initiated. Otherwise, LIN1 times out after 512  $\mu s$  and LIN2 Mode is entered.

In LIN2 Mode, the current source is incremented. If  $V_{OUT}$  fails to reach  $V_{IN}$ -300 mV after 1024  $\mu s$ , a fault condition is declared and the device waits 20 ms to attempt an automatic restart.

#### Soft-Start (SS) Mode

Upon the successful completion of LIN Mode ( $V_{OUT} \ge V_{IN}$ -300 mV), the regulator begins switching with boost pulses current limited to 50% of nominal level.

During SS Mode, if  $V_{OUT}$  fails to reach regulation during the SS ramp sequence for more than 64  $\mu$ s, a fault is declared. If large  $C_{OUT}$  is used, the reference is automatically stepped slower to avoid excessive input current draw.

#### **Boost (BST) Mode**

This is a normal operating mode of the regulator.

#### Pass-Through (PT) Mode

The device allows the user to force the device in Forced Pass-Through Mode through the EN pin. If the EN pin is pulled HIGH, the device starts operating in Boost Mode. Once the EN pin is pulled LOW, the device is forced into Pass-Through Mode. To disable the device, the input supply voltage must be removed. The device cannot startup in Forced Pass-Through Mode (see Figure 21). During startup, keep the EN pulled HIGH for at least 350 µs before pulling it LOW in order to make sure that the device enters Pass-Through Mode realiably.

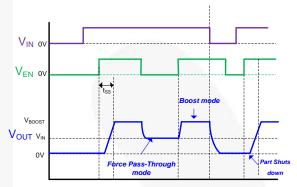


Figure 21. Pass-Through Profile

#### **Current Limit Protection**

The FAN48619 has valley current limit protection in case of overload situations. The valley current limit will prevent high current from causing damage to the IC and the inductor. The current limit is halved during soft-start.

When starting into a fault condition, the input current will be limited by LIN1 and Lin2 current threshold.

#### **Fault State**

The regulator enters Fault State under any of the following conditions:

- V<sub>OUT</sub> fails to achieve the voltage required to advance from LIN Mode to SS Mode.
- V<sub>OUT</sub> fails to achieve the voltage required to advance from SS Mode to BST Mode.
- Boost current limit triggers for 2 ms during BST Mode.
- V<sub>IN</sub> V<sub>OUT</sub> > 300 mV; this fault can occur only after successful completion of the soft-start sequence.
- $\blacksquare$   $V_{IN} < V_{UVLO}$ .

Once a fault is triggered, the regulator stops switching and presents a high-impedance path between VIN and VOUT. After waiting 20 ms, an automatic restart is attempted.

## **Over-Temperature**

The regulator shuts down if the die temperature exceeds 150°C and restarts when the IC cools by ~20°C.

## **Layout Recommendations**

The layout recommendations below highlight various top-copper pours by using different colors.

To minimize spikes at VOUT, C<sub>OUT</sub> must be placed as close as possible to PGND and VOUT, as shown in Figure 22.

For best thermal performance, maximize the pour area for all planes other than SW. The ground pour, especially, should fill all available PCB surface area and be tied to internal layers with a cluster of thermal vias.

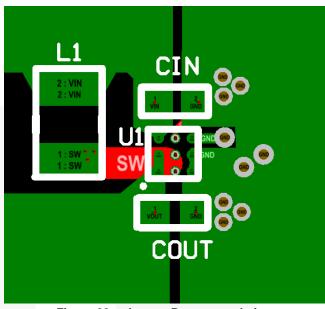
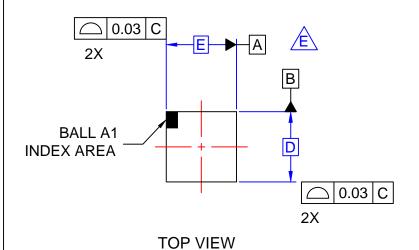


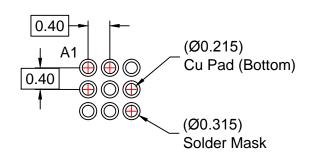
Figure 22. Layout Recommendation

The following information applies to the WLCSP package dimensions on the next page:

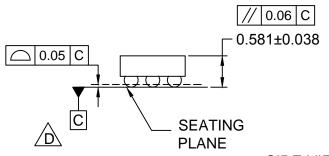
## **Product-Specific Package Dimensions**

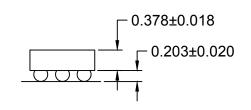
Product	D	E	X	Y
FAN48619UC50X	1.215 ±0.030 mm	1.215 ±0.030 mm	0.2075 mm	0.2075 mm





## RECOMMENDED LAND PATTERN (NSMD PAD TYPE)





#### SIDE VIEWS

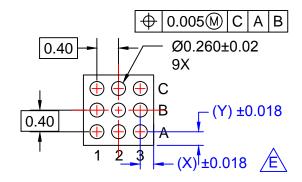
#### **NOTES**

- A. NO JEDEC REGISTRATION APPLIES.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCE PER ASME Y14.5M, 2009.
- D. DATUM C IS DEFINED BY THE

  SPHERICAL CROWNS OF THE BALLS.

  E. FOR DIMENSIONS D,E,X, AND Y SEE
  - PRODUCT DATASHEET.

    F. DRAWING FILNAME: MKT-UC009Ak rev3



**BOTTOM VIEW** 

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